

NCE P-Channel Enhancement Mode Power MOSFET

Description

The NCE01P18D uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications. It is ESD protested.

General Features

- V_{DS} =-100V,I_D =-18A $R_{DS(ON)} < 100 m\Omega @ V_{GS} = -10V$ (Typ:85m Ω)
- Super high dense cell design
- Advanced trench process technology
- Reliable and rugged
- High density cell design for ultra low on-Resistance

Application

- Power management in notebook computer
- Portable equipment and battery powered systems

100% UIS TESTED!

100% ΔVds TESTED!

Schematic diagram NCE NCE01P18D XXXXX Marking and pin assignment

D



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE01P18D	NCE01P18D	TO-263-2L	Ø330mm	21mm	800 units

Absolute Maximum Ratings (T_c=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	Vds	-100	V	
Gate-Source Voltage	Vgs	±20	V	
Drain Current-Continuous	Ι _D	-18	A	
Drain Current-Continuous(T _C =100℃)	I _D (100℃)	-12	A	
Pulsed Drain Current	I _{DM}	-72	A	
Maximum Power Dissipation	PD	70	W	
Derating factor		0.47	W/°C	
Operating Junction and Storage Temperature Range	T _J ,T _{STG}	-55 To 175	°C	

Thermal Characteristic

Thermal Resistance, Junction-to-Case (Note 2)	R _{θJc}	2.14	°C/W
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Electrical Characteristics (T_c=25°C unless otherwise noted)

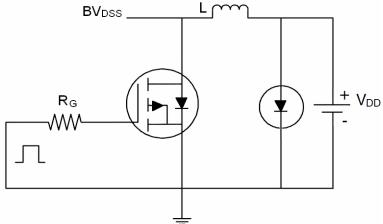
Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =-250µA	-100	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-100V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±20	μA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =-250µA	-1	-1.9	-3	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-10V, I _D =-16A	-	85	100	mΩ
Forward Transconductance	g fs	V _{DS} =-50V,I _D =-10A	5	-	-	S
Dynamic Characteristics (Note4)		·				
Input Capacitance	C _{lss}	V _{DS} =-25V,V _{GS} =0V,	-	1300	-	PF
Output Capacitance	C _{oss}		-	400	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1.0MHz	-	240	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}		-	16	-	nS
Turn-on Rise Time	tr	V _{DD} =-50V,I _D =-16A V _{GS} =-10V,R _{GEN} =9.1Ω	-	73	-	nS
Turn-Off Delay Time	t _{d(off)}		-	34	-	nS
Turn-Off Fall Time	t _f		-	57	-	nS
Total Gate Charge	Qg	V _{DS} =-80V,I _D =-16A,	-	61	-	nC
Gate-Source Charge	Q _{gs}		-	14	-	nC
Gate-Drain Charge	Q _{gd}	V _{GS} =-10V	-	29	-	nC
Drain-Source Diode Characteristics					L	
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =-10A	-	-	-1.2	V
Diode Forward Current (Note 2)	Is	-	-	-	-18	A
Reverse Recovery Time	t _{rr}	TJ = 25°C, IF =-16A	-	88.3	-	nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs ^(Note3)	-	65.9	-	nC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

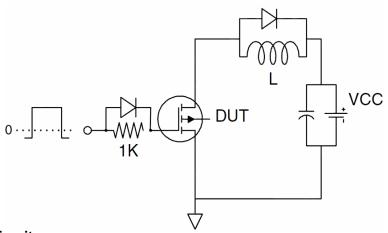
- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board, $t \le 10$ sec.
- **3.** Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production
- **5.** EAS condition: Tj=25 $^\circ C$,V_DD=-50V,V_G=-10V,L=0.5mH,Rg=25\Omega



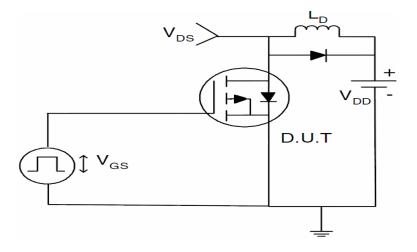
Test Circuit 1) E_{AS} Test Circuit



2) Gate Charge Test Circuit

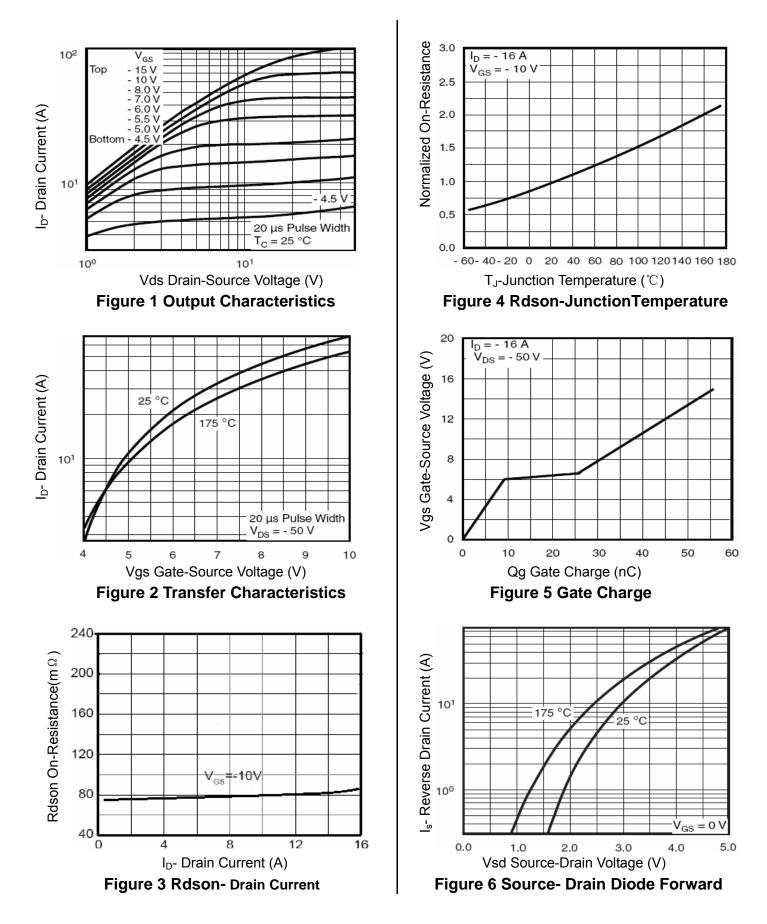


3) Switch Time Test Circuit



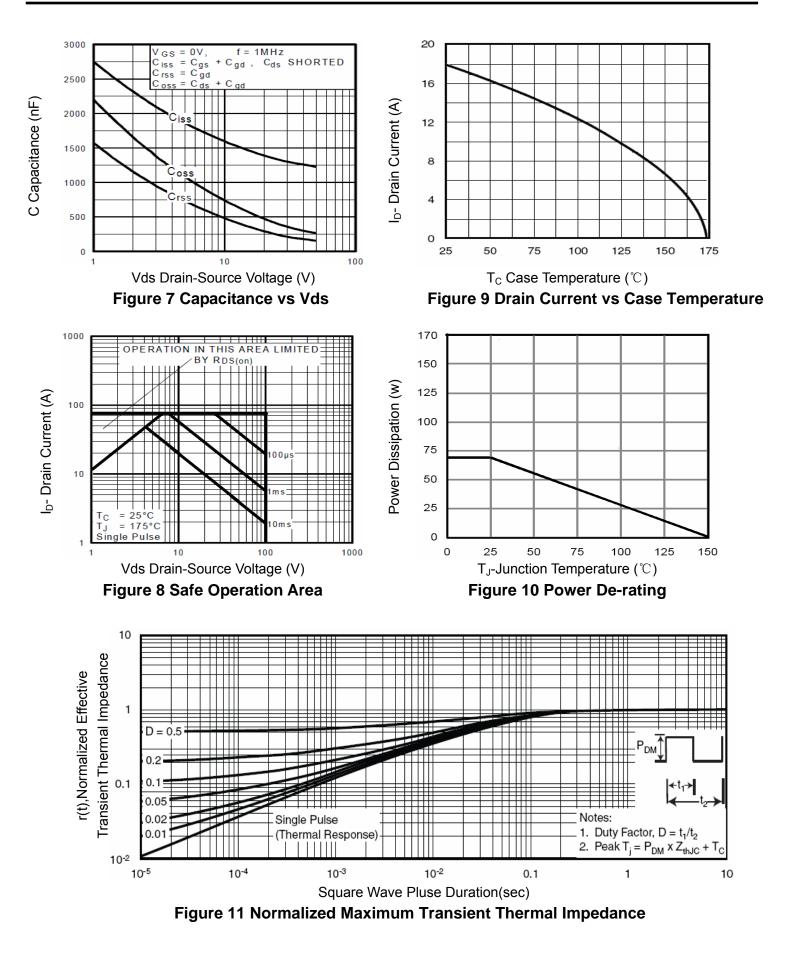


Typical Electrical and Thermal Characteristics (Curves)



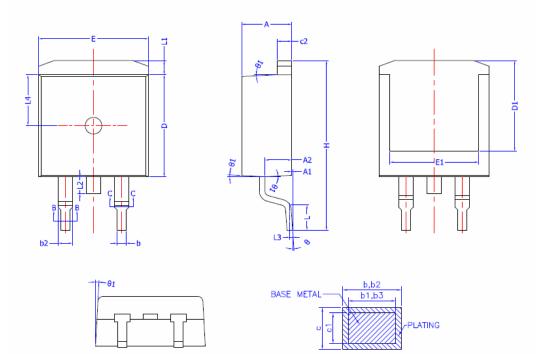


http://www.ncepower.com





TO-263-2L Package Information



COMMON DIMENSIONS (UNITS OF MEASURE =MILLIMETER)

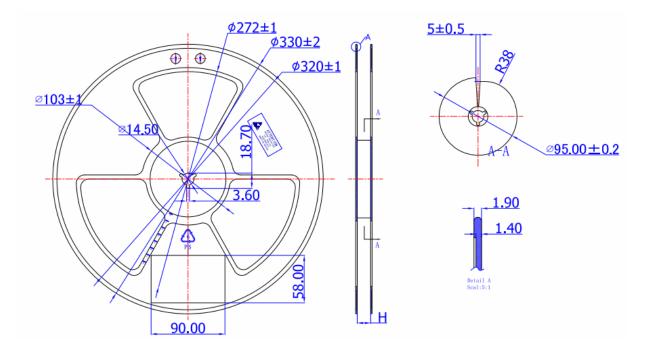
SECTION B-B&C-C

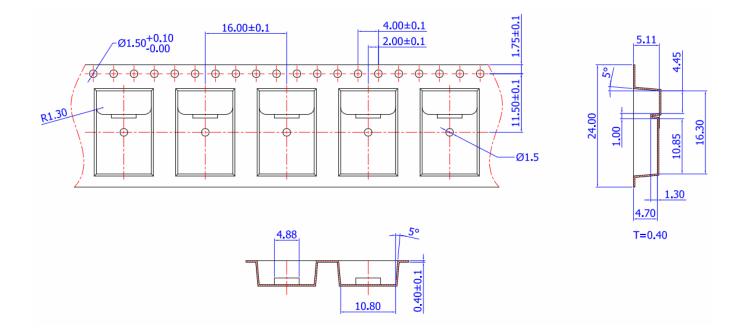
<u> </u>	5 OF FILAS			
SYMBOL	MIN	NOM	MAX	
Α	4.40	4.50	4.60	
A1	0	0.10	0.25	
A2	2,20	2,40	2,60	
b	0,76		0,89	
b1	0,75	0,80	0,85	
b2	1,23		1,37	
b3	1,22	1,27	1,32	
с	0,47		0,60	
c1	0,46	0,51	0.56	
c2	1,25	1,30	1.35	
D	9,10	9,20	9.30	
D1	8,00		—	
E	9,80	9,90	10.00	
E1	7.80	—	—	
е	2.54 BSC			
H L	14,90	15,30	15.70	
L	2.00	2,30	2.60	
L1	1.17	1.27	1.40	
L2			1,75	
L3	0.25BSC			
L4	4.60 REF			
θ	0°		8°	
θ1	1°	3°	5°	



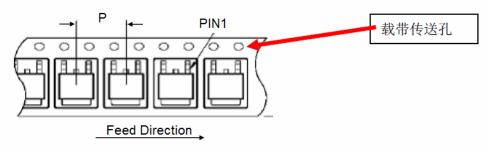
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NCE01P18D





注:产品编入卷盘中时,产品第一支脚(PIN 1)方向朝向载带传送孔。如下图所示。





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